



CHENMKO ENTERPRISE CO.,LTD

CHM4948JPT

SURFACE MOUNT

Dual P-Channel Enhancement Mode Field Effect Transistor

VOLTAGE 60 Volts CURRENT 3.1 Ampere

Lead free devices

APPLICATION

- * Servo motor control.
- * Power MOSFET gate drivers.
- * Other switching applications.

FEATURE

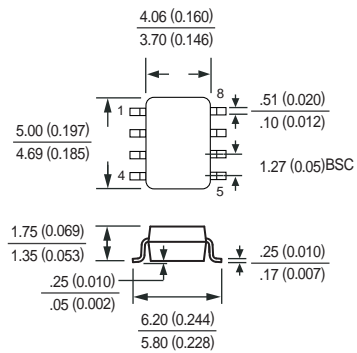
- * Small flat package. (SO-8)
- * Super high dense cell design for extremely low $R_{DS(ON)}$.
- * High power and current handling capability.
- * Lead free product is acquired.

CONSTRUCTION

- * P-Channel Enhancement



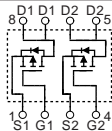
SO-8



Dimensions in millimeters

SO-8

CIRCUIT



Absolute Maximum Ratings $T_A = 25^\circ\text{C}$ unless otherwise noted

| Symbol | Parameter | CHM4948JPT | Units |
|-----------|------------------------------------|------------|------------------|
| V_{DSS} | Drain-Source Voltage | -60 | V |
| V_{GSS} | Gate-Source Voltage | ± 20 | V |
| I_D | Maximum Drain Current - Continuous | -3.1 | A |
| | - Pulsed (Note 3) | -20 | |
| P_D | Maximum Power Dissipation | 2000 | mW |
| T_J | Operating Temperature Range | -55 to 150 | $^\circ\text{C}$ |
| T_{STG} | Storage Temperature Range | -55 to 150 | $^\circ\text{C}$ |

- Note : 1. Surface Mounted on FR4 Board , $t \leq 10\text{sec}$
 2. Pulse Test , Pulse width $\leq 300\mu\text{s}$, Duty Cycle $\leq 2\%$
 3. Repetitive Rating , Pulse width limited by maximum junction temperature
 4. Guaranteed by design , not subject to production trsting

Thermal characteristics

| | | | |
|-----------------|--|------|--------------------|
| $R_{\theta JA}$ | Thermal Resistance, Junction-to-Ambient (Note 1) | 62.5 | $^\circ\text{C/W}$ |
|-----------------|--|------|--------------------|

2006-02

RATING CHARACTERISTIC CURVES (CHM4948JPT)

Electrical Characteristics $T_A = 25^\circ\text{C}$ unless otherwise noted

| Symbol | Parameter | Conditions | Min | Typ | Max | Units |
|--------|-----------|------------|-----|-----|-----|-------|
|--------|-----------|------------|-----|-----|-----|-------|

OFF CHARACTERISTICS

| | | | | | | |
|------------|---------------------------------|--|-----|--|------|---------------|
| BV_{DSS} | Drain-Source Breakdown Voltage | $V_{GS} = 0\text{ V}, I_D = -250\ \mu\text{A}$ | -60 | | | V |
| I_{DSS} | Zero Gate Voltage Drain Current | $V_{DS} = -60\text{ V}, V_{GS} = 0\text{ V}$ | | | -2 | μA |
| I_{GSSF} | Gate-Body Leakage | $V_{GS} = 20\text{ V}, V_{DS} = 0\text{ V}$ | | | +100 | nA |
| I_{GSSR} | Gate-Body Leakage | $V_{GS} = -20\text{ V}, V_{DS} = 0\text{ V}$ | | | -100 | nA |

ON CHARACTERISTICS (Note 2)

| | | | | | | |
|--------------|-----------------------------------|---|----|-----|-----|------------------|
| $V_{GS(th)}$ | Gate Threshold Voltage | $V_{DS} = V_{GS}, I_D = -250\ \mu\text{A}$ | -1 | | -3 | V |
| $R_{DS(ON)}$ | Static Drain-Source On-Resistance | $V_{GS} = -10\text{ V}, I_D = -3.1\text{ A}$ | | 90 | 120 | $\text{m}\Omega$ |
| | | $V_{GS} = -4.5\text{ V}, I_D = -2.8\text{ A}$ | | 120 | 150 | |
| g_{FS} | Forward Transconductance | $V_{DS} = -15\text{ V}, I_D = -3.1\text{ A}$ | | 7 | | S |

SWITCHING CHARACTERISTICS (Note 4)

| | | | | | | |
|-----------|--------------------|--|--|----|-----|----|
| Q_g | Total Gate Charge | $V_{DS} = -30\text{ V}, I_D = -3.1\text{ A}$ $V_{GS} = -10\text{ V}$ | | 21 | 29 | nC |
| Q_{gs} | Gate-Source Charge | | | 3 | | |
| Q_{gd} | Gate-Drain Charge | | | 4 | | |
| t_{on} | Turn-On Time | $V_{DD} = -30\text{ V}$ $I_D = -1.0\text{ A}, V_{GS} = -10\text{ V}$ $R_{GEN} = 6\ \Omega$ | | 13 | 45 | nS |
| t_r | Rise Time | | | 9 | 30 | |
| t_{off} | Turn-Off Time | | | 48 | 150 | |
| t_f | Fall Time | | | 22 | 75 | |

DRAIN-SOURCE DIODE CHARACTERISTICS AND MAXIMUM RATINGS

| | | | | | | |
|----------|------------------------------------|---|--|--|------|---|
| I_S | Drain-Source Diode Forward Current | (Note 1) | | | -2.0 | A |
| V_{SD} | Drain-Source Diode Forward Voltage | $I_S = -2.0\text{ A}, V_{GS} = 0\text{ V}$ (Note 2) | | | -1.2 | V |